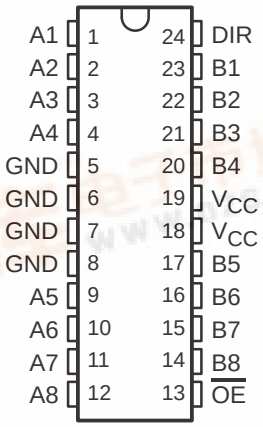
- 3-State Outputs Drive Bus Lines Directly
- Inputs Are TTL-Voltage Compatible
- Flow-Through Architecture Optimizes PCB Layout
- Center-Pin V_{CC} and GND Configurations Minimize High-Speed Switching Noise
- *EPIC*™ (Enhanced-Performance Implanted CMOS) 1-μm Process
- 500-mA Typical Latch-Up Immunity at 125°C
- Package Options Include Plastic Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, and Standard Plastic 300-mil DIPs (NT)

DB, DW, NT, OR PW PACKAGE
(TOP VIEW)



description

The octal bus transceiver is designed for asynchronous two-way communication between data buses. The control-function implementation minimizes external timing requirements.

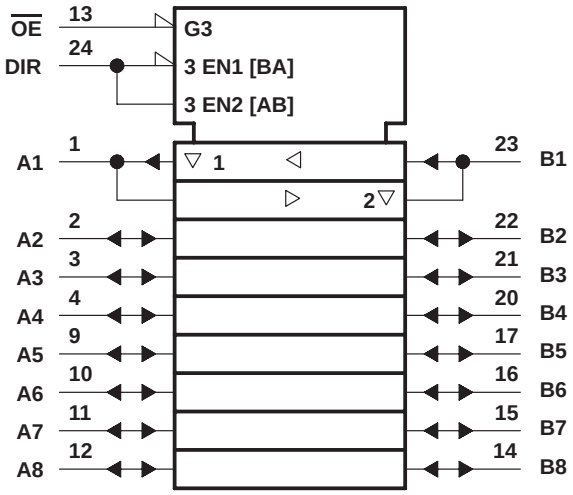
The device allows data transmission from the A bus to the B bus or from the B bus to the A bus, depending on the logic level at the direction-control (DIR) input. The output-enable ($\overline{OE}$) input can be used to disable the device so that the buses are effectively isolated.

The 74ACT11245 is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

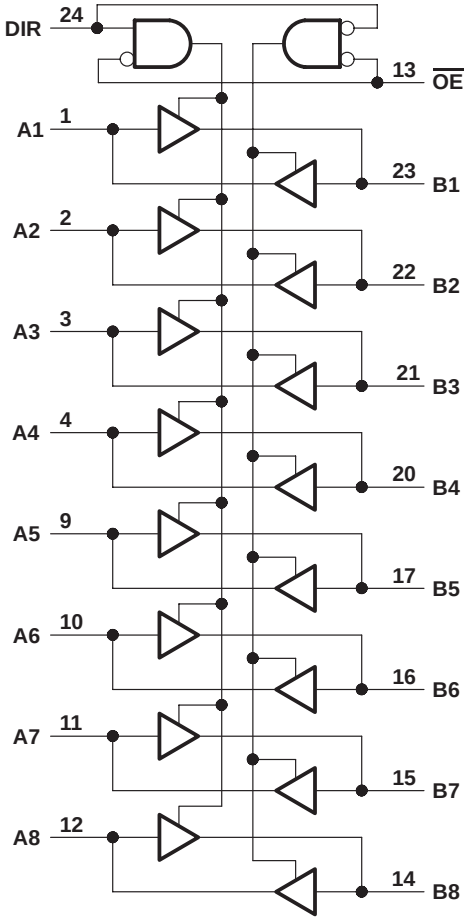
OUTPUT ENABLE $\overline{OE}$	DIRECTION CONTROL DIR	OUTPUT
L	L	B data to A bus
L	H	A data to B bus
H	X	Isolation

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 7 V
Input voltage range, V_I (see Note 1) . . . . . –0.5 V to V_{CC} + 0.5 V
Output voltage range, V_O (see Note 1) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0 or V_I > V_{CC}) . . . . . ±20 mA
Output clamp current, I_{OK} (V_O < 0 or V_O > V_{CC}) . . . . . ±50 mA
Continuous output current, I_O (V_O = 0 to V_{CC}) . . . . . ±50 mA
Continuous current through V_{CC} or GND . . . . . ±200 mA
Maximum power dissipation at T_A = 55°C (in still air) (see Note 2): DB package . . . . . 0.65 W
DW package . . . . . 1.7 W
NT package . . . . . 1.3 W
PW package . . . . . 0.7 W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils, except for the NT package, which has a trace length of zero.

recommended operating conditions

		MIN	MAX	UNIT
V_{CC}	Supply voltage	4.5	5.5	V
V_{IH}	High-level input voltage	2		V
V_{IL}	Low-level input voltage		0.8	V
V_I	Input voltage	0	V_{CC}	V
V_O	Output voltage	0	V_{CC}	V
I_{OH}	High-level output current		–24	mA
I_{OL}	Low-level output current		24	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	0	10	ns/V
T_A	Operating free-air temperature	–40	85	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}	T_A = 25°C			MIN	MAX	UNIT
				MIN	TYP	MAX			
V_{OH}		I_{OH} = –50 μA	4.5 V	4.4			4.4		V
			5.5 V	5.4			5.4		
		I_{OH} = –24 mA	4.5 V	3.94			3.8		
			5.5 V	4.94			4.8		
		I_{OH} = –75 mA†	5.5 V				3.85		
V_{OL}		I_{OL} = 50 μA	4.5 V			0.1		0.1	V
			5.5 V			0.1		0.1	
		I_{OL} = 24 mA	4.5 V			0.36		0.44	
			5.5 V			0.36		0.44	
		I_{OL} = 75 mA†	5.5 V					1.65	
I_{OZ}	A or B ports‡	V_O = V_{CC} or GND	5.5 V			±0.5		±5	μA
I_I	$\overline{OE}$ or DIR	V_I = V_{CC} or GND	5.5 V			±0.1		±1	μA
I_{CC}		V_I = V_{CC} or GND, I_O = 0	5.5 V			8		80	μA
ΔI_{CC}§		One input at 3.4 V, Other inputs at GND or V_{CC}	5.5 V			0.9		1	mA
C_i		V_I = V_{CC} or GND	5 V		4				pF
C_o		V_O = V_{CC} or GND	5 V		12				pF

† Not more than one output should be tested at a time, and the duration of the test should not exceed 10 ms.
‡ For I/O ports, the parameter I_{OZ} includes the input leakage current.
§ This is the increase in supply current for each input that is at one of the specified TTL voltage levels rather than 0 V or V_{CC}.

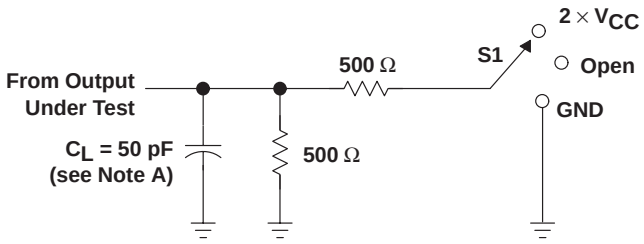
switching characteristics over recomended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	T_A = 25°C			MIN	MAX	UNIT
			MIN	TYP	MAX			
t_{PLH}	A or B	B or A	1.5	6.2	9.2	1.5	10	ns
t_{PHL}			1.5	5.4	8.6	1.5	9.1	
t_{PZH}	$\overline{OE}$	A or B	1.5	8.1	12	1.5	13.2	ns
t_{PZL}			1.5	8.2	11.7	1.5	12.9	
t_{PHZ}	$\overline{OE}$	A or B	1.5	9.3	11.8	1.5	12.9	ns
t_{PLZ}			1.5	9.8	12.9	1.5	13.9	

operating characteristics, V_{CC} = 5 V, T_A = 25°C

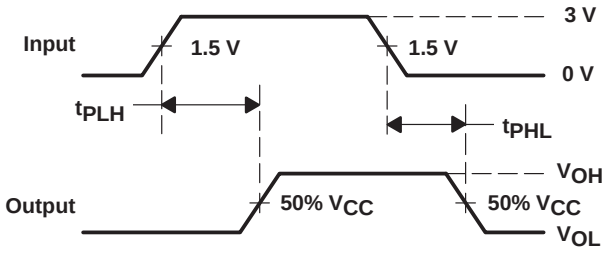
PARAMETER			TEST CONDITIONS	TYP	UNIT
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	C_L = 50 pF, f = 1 MHz	66	pF
		Outputs disabled		19	

PARAMETER MEASUREMENT INFORMATION

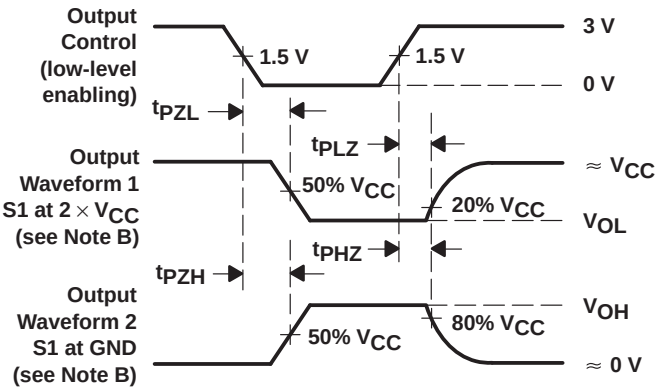


TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	GND

LOAD CIRCUIT



VOLTAGE WAVEFORMS



VOLTAGE WAVEFORMS

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_r = 3 ns, t_f = 3 ns.
D. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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